

What is claimed is:

1. A bidirectional semiconductor component having two symmetrical MOS transistor structures integrated laterally in a substrate and connected antiseriably, their drain terminals being connected to one another, wherein a zone (28) having the same type of conductivity as the drain region yet a higher doping than that of the drain region (12) is situated upstream from a pn junction (22) of one of the MOS transistors (26) in a junction area with the drain region (12).
2. The bidirectional semiconductor component according to Claim 1, wherein the drain region (12) and the zone (28) are n-doped.
3. The bidirectional semiconductor component according to one of the preceding claims, wherein the drain region (12) is situated on a layer (42) having a doping of the opposite type of conductivity from the drain region (12).
4. The bidirectional semiconductor component according to Claim 3, wherein the layer (42) is made up of partial layers (44, 46) having stepped doping.
5. A use of a bidirectional semiconductor component according to one of Claims 1 through 4 as short-circuit switch (40) for short circuiting a primary winding (36) of an ignition coil (30) in an ignition power module of an ignition system of an internal combustion engine.
6. The use according to Claim 5, characterized by a time-staggered activation of the gate terminals (20, 20') of the MOS transistor structures (26, 26'), the MOS transistor (26), which blocks a higher voltage (U_{CE}), being activated later.
7. The use according to Claim 6, wherein the time-staggered activation is accomplished by interconnecting a capacitor (bootstrap).

8. The use according to Claim 6,
wherein the ~~time~~-staggered activation is accomplished by a time control.

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